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TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Hisato OYAMATSU

Serial No.: 09/917,775

Filed: July 31, 2001

For: SEMICONDUCTOR DEVICE



Atty. Docket No.: 002372.00027

Group Art Unit: 2811

Examiner: Hu, S.

Confirmation No.: 1487

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

PETITION FOR EXTENSION OF TIME

This paper is responsive to the Office Action mailed May 22, 2002. Applicant requests a two (2) month extension of time until October 22, 2002. The Commissioner is authorized to charge our Deposit Account No. 19-0733 in the amount of \$400.00 (a Fee Transmittal is attached). If additional fees are required or if an overpayment is made, the Commissioner is authorized to charge or credit our Deposit Account No. 19-0733, accordingly.

In response to the Office Action mailed May 22, 2002, please amend the instant application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 2, lines 4-7:

In case of Fig. 9A, an n^+ diffusion layer 15, which is a device region, is formed on the surface part of the p-well 13, but no device region exists in the opposite position in the n-well side. This is called an open space.